(Tc = 25°C unless otherwise specified)

$V_{DS,max}$	Drain source voltage	1200	V	V_{GS} = 0V, I_D = 100μA	
$V_{GS,max}$	Gate source voltage	-8 /+19	V	Absolute maximum values	Note1
V_{GSop}	Gate source voltage	-4 /+15	V	Recommended operational values	
I_D	Continuous drain current	20 14	A	V_{GS} = 15V, T_C = 25˚C V_{GS} = 15V, T_C = 100˚C	Fig.19
$I_{D(pulse)}$	Pulsed				

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Datasheet

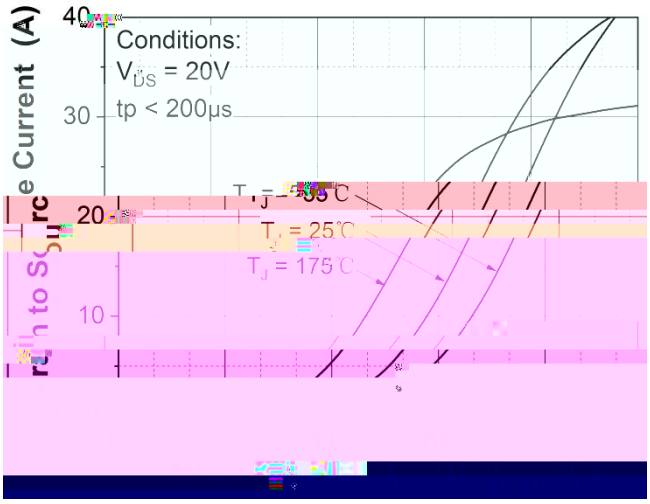


Figure 7. Transfer characteristic for various junction temperatures

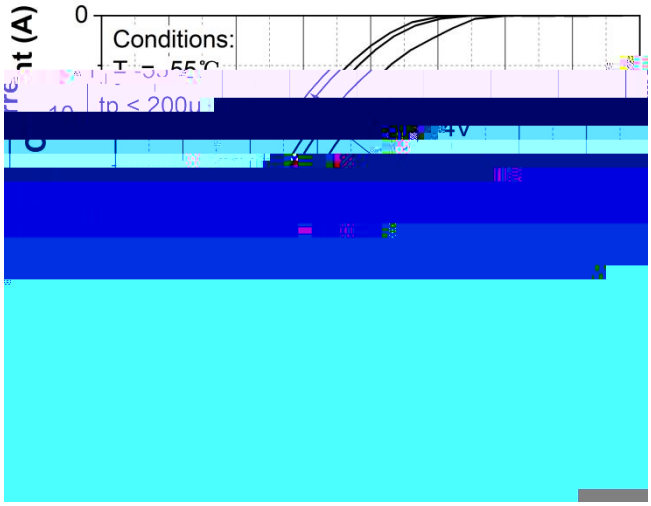


Figure 8. Body diode characteristic at T_J = -55 ºC

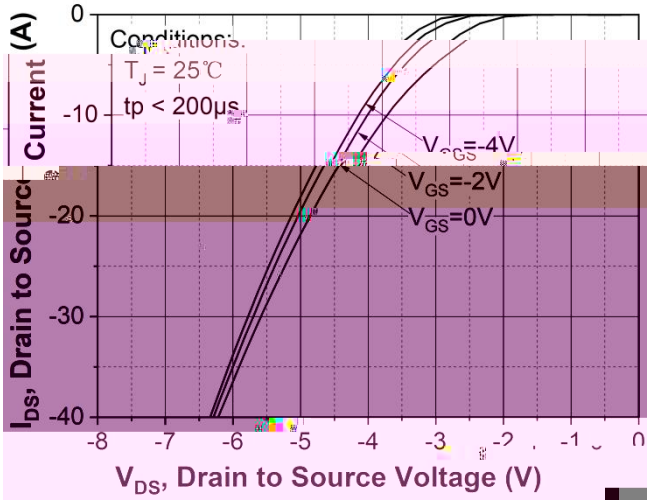


Figure 9. Body diode characteristic at T_J = 25 ºC

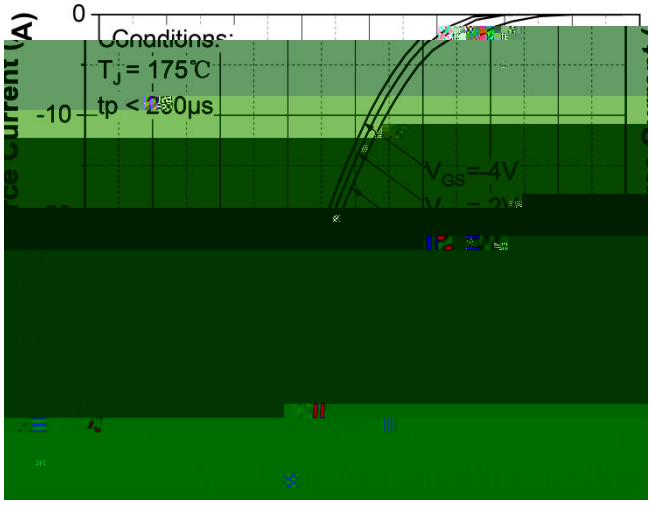


Figure 10. Body diode characteristic at T_J = 175ºC

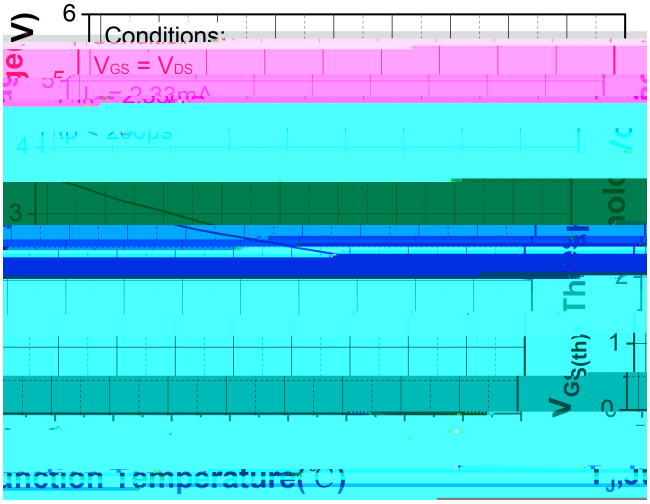


Figure 11. Threshold voltage vs. temperature

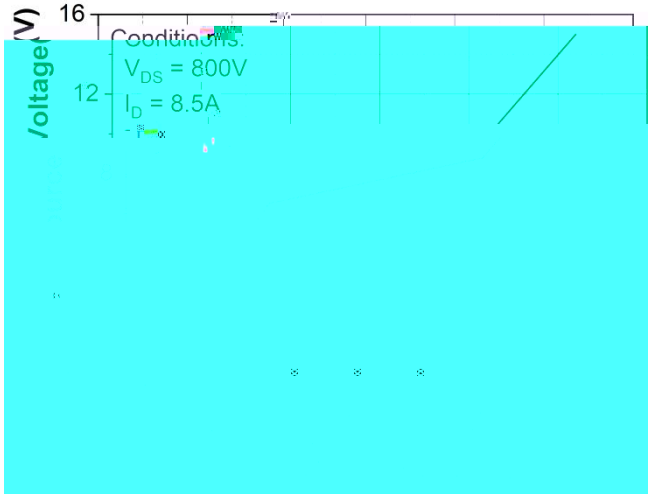


Figure 12. Gate charge characteristic

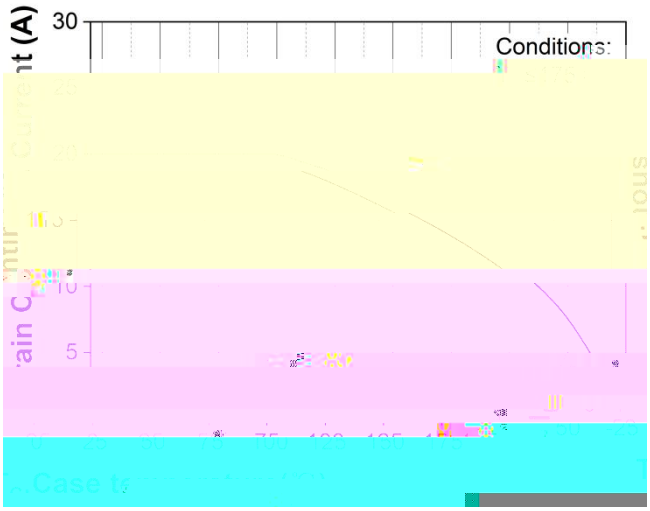


Figure 19. Continuous drain current derating vs. case temperature

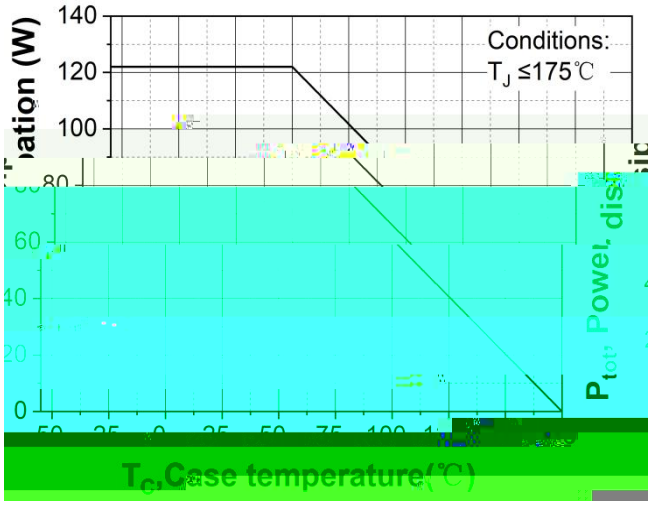


Figure 20. Maximum power dissipation derating vs. case temperature

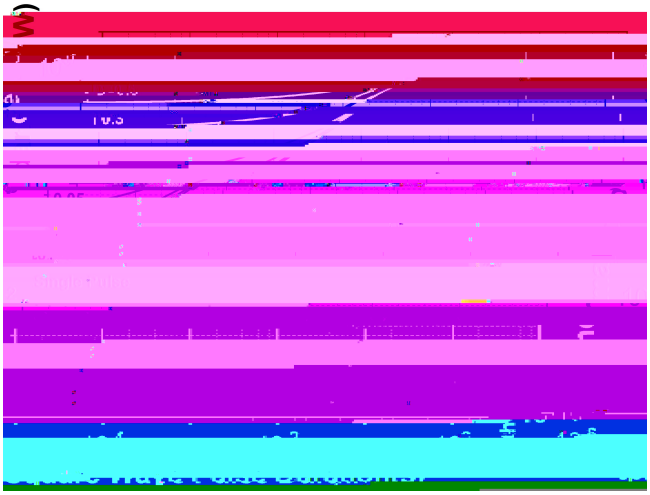


Figure 21. Transient thermal impedance (junction - case)

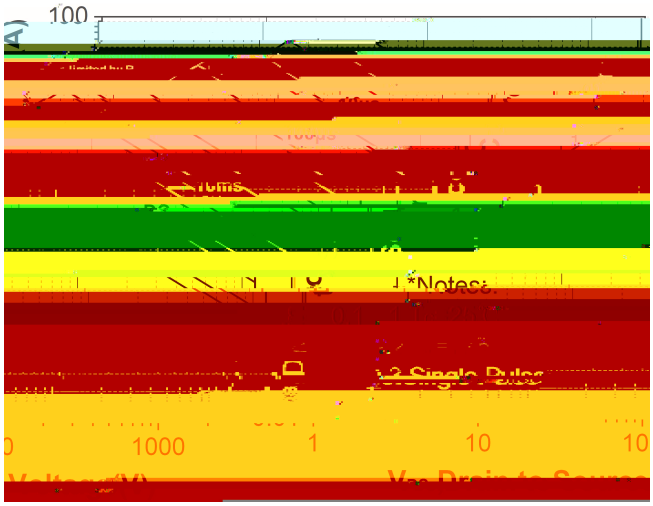


Figure 22. Safe operating area

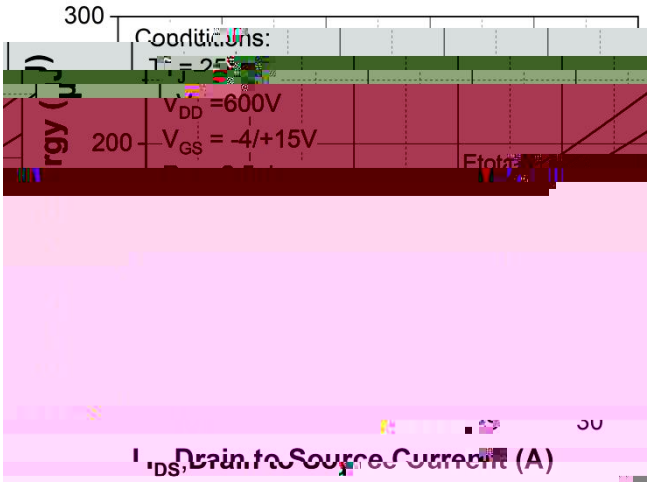


Figure 23. Clamped Inductive switching energy vs. drain current (V_{DD} = 600V)

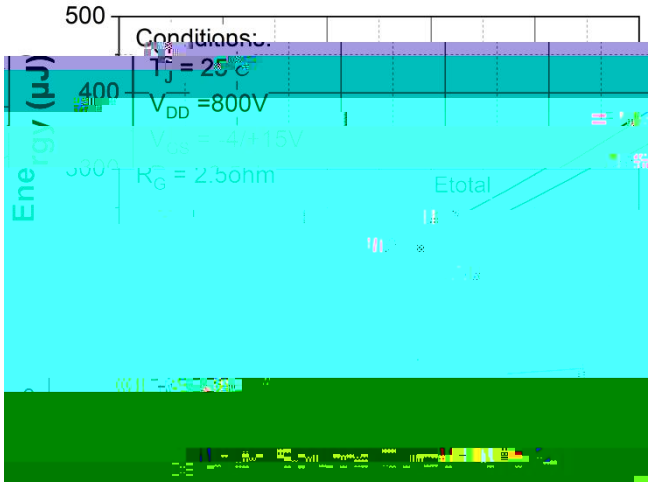


Figure 24. Clamped inductive switching energy vs. drain current (V_{DD} = 800V)

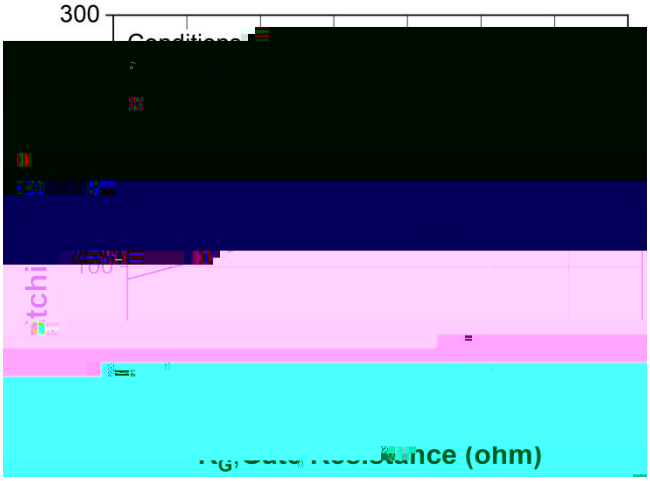


Figure 25. Clamped inductive switching energy vs. R_G(ext)

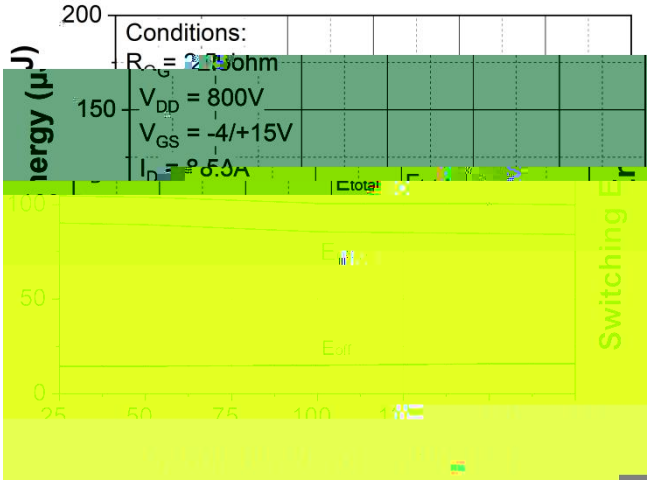


Figure 26. Clamped inductive switching energy vs. temperature

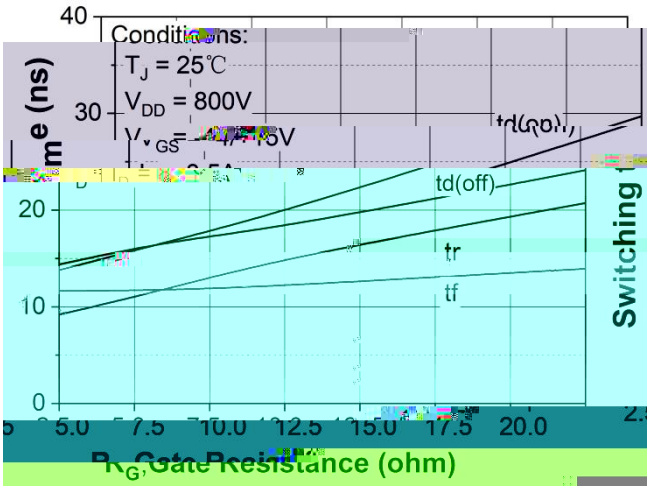


Figure 27. Switching times vs. R_G(ext)

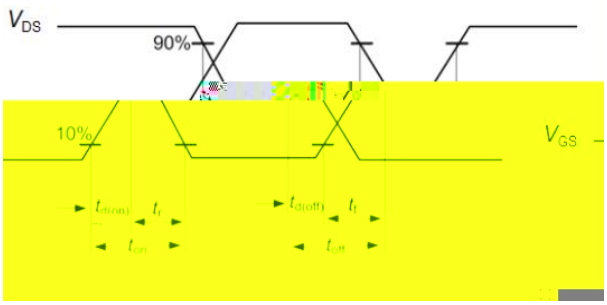


Figure A. Definition of switching times

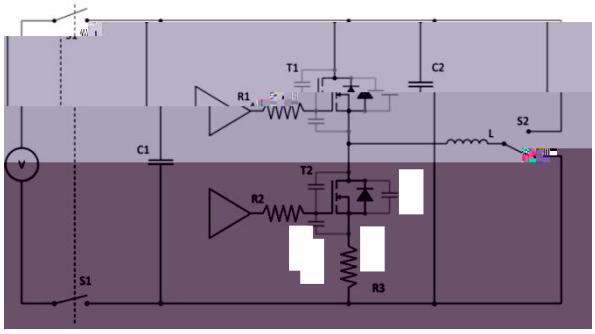


Figure B. Dynamic test circuit

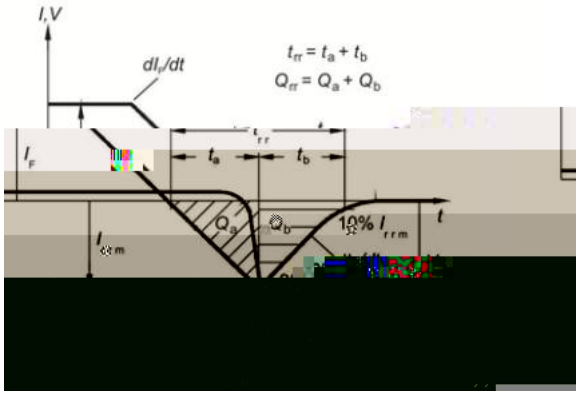


Figure C. Definition of body diode switching characteristics